NEC
ELECTRON DEVICE

N-CHANNEL MOS FIELD EFFECT POWER TRANSISTOR

2SK707

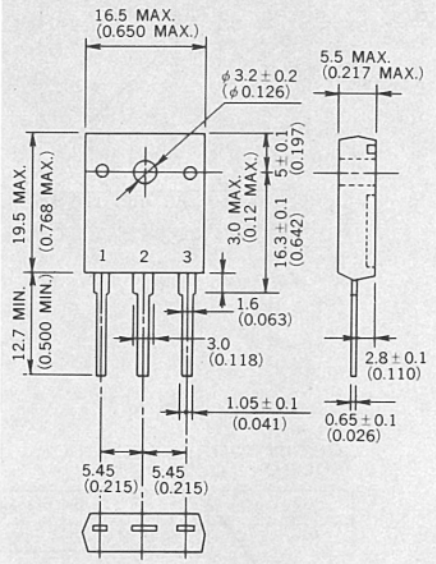
Phase-out/Discontinued

DESCRIPTION The 2SK707 is N-channel MOS Field Effect Power Transistor designed for switching power supplies, DC-DC converters.

FEATURES

- Suitable for switching power supplies, actuater controls, and pulse circuits.
- Low $R_{DS(on)}$
- No second breakdown

PACKAGE DIMENSIONS
in millimeters (inches)



1. Gate
2. Drain (Fin)
3. Source

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

- Storage Temperature . . . . . −55 to +150 °C
- Channel Temperature . . . . . 150 °C Maximum

Maximum Power Dissipation (T_c = 25 °C)

- Total Power Dissipation . . . . . 120 W

Maximum Voltages and Currents (T_a = 25 °C)

- V_{DSS} Drain to Source Voltage . . . . . 250 V
- V_{GSS} Gate to Source Voltage. . . . . ±20 V
- $I_{D(DC)}$ Drain Current (DC) . . . . . ±25 A
- $I_{D(pulse)}$ Drain Current (pulse)* . . . . . ±100 A

* PW ≦ 100 μs, Duty Cycle ≦ 2 %

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
I_{DSS}	Drain Leakage Current			100	μA	V_{DS} = 250 V, V_{GS} = 0
I_{GSS}	Gate to Source Leakage Current			±100	nA	V_{GS} = ±20 V, V_{DS} = 0
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1.5		3.5	V	V_{DS} = 10 V, I_D = 1 mA
$\|y_{fs}\|$	Forward Transfer Admittance	5.0			S	V_{DS} = 10 V, I_D = 13 A
$R_{DS(on)}$	Drain to Source On-State Resistance		0.12	0.15	Ω	V_{GS} = 10 V, I_D = 13 A
C_{iss}	Input Capacitance		2950		pF	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz
C_{oss}	Output Capacitance		990		pF	
C_{rss}	Reverse Transfer Capacitance		450		pF	
$t_{d(on)}$	Turn-On Delay Time		25		ns	I_D = 13 A, V_{DD} ≒ 150 V, $V_{GS(on)}$ = 10 V, R_L = 11.5 Ω, R_{in} = 10 Ω
t_r	Rise Time		85		ns	
$t_{d(off)}$	Turn-Off Delay Time		115		ns	
t_f	Fall Time		85		ns	

NEC cannot assume any responsibility for any circuits shown or represent that they are free from patent infringement.

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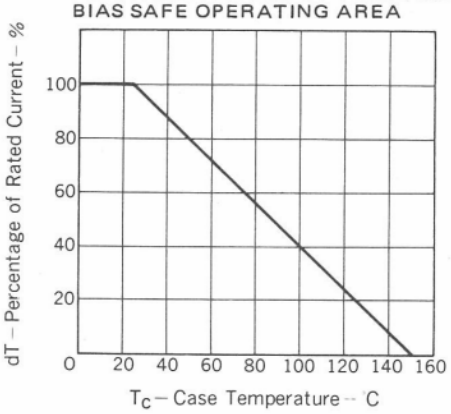
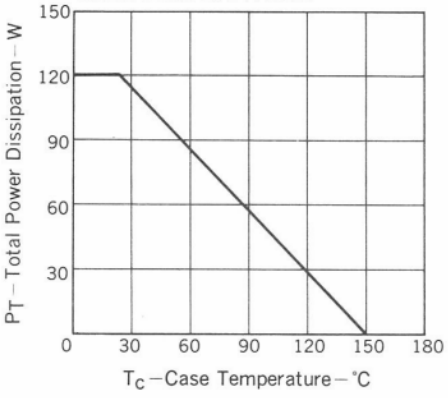
TYPICAL CHARACTERISTICS (T_a = 25 °C)

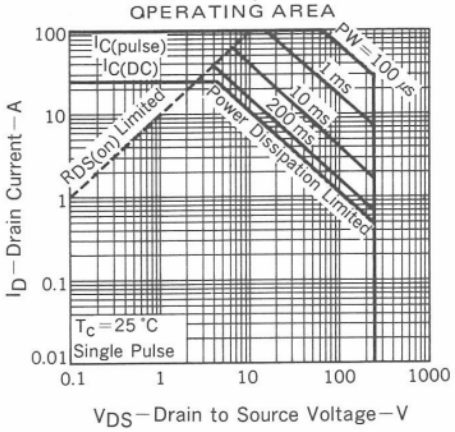
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



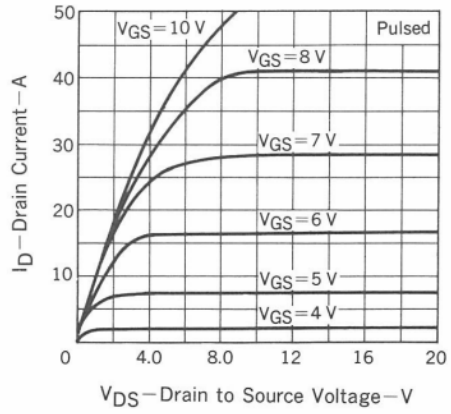
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



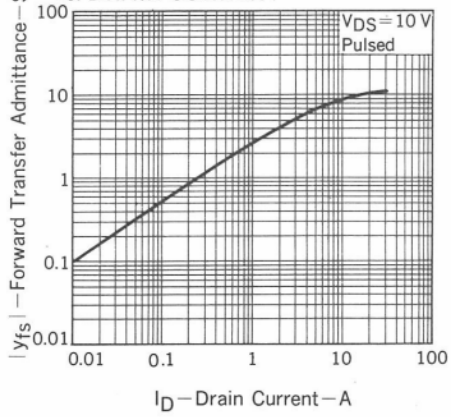
FORWARD BIAS SAFE OPERATING AREA



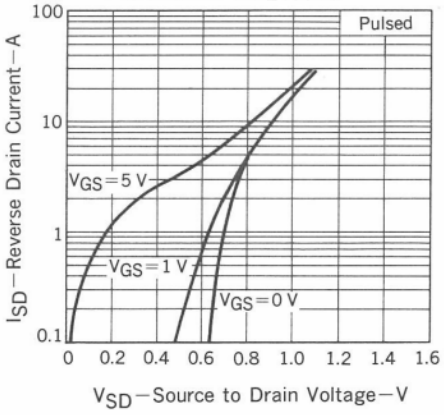
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



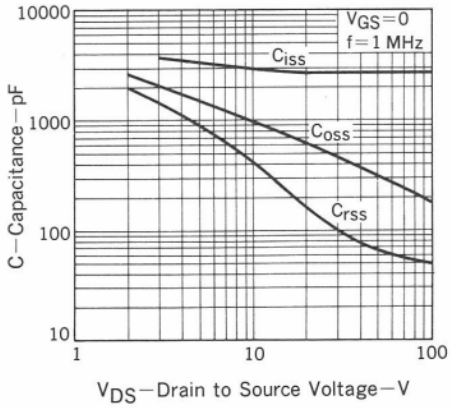
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



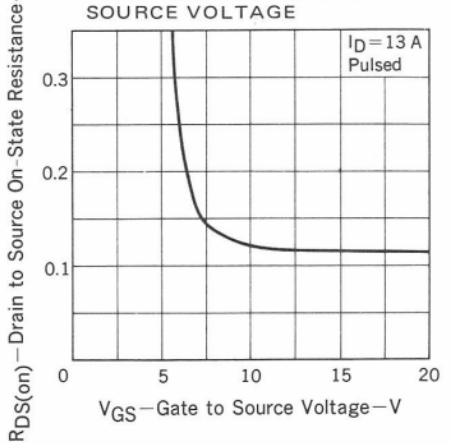
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



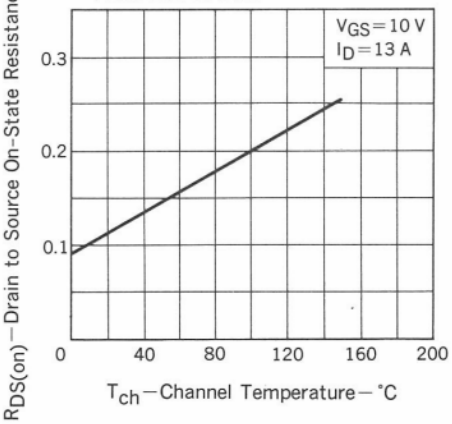
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



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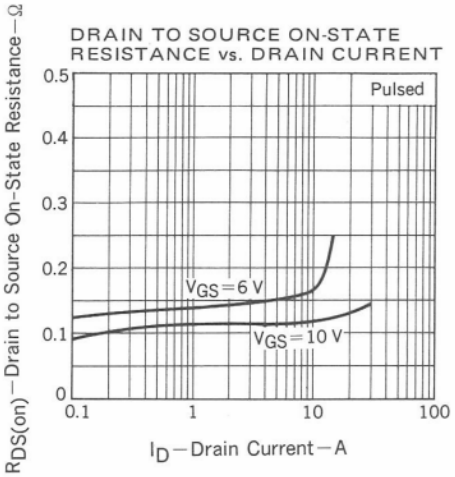
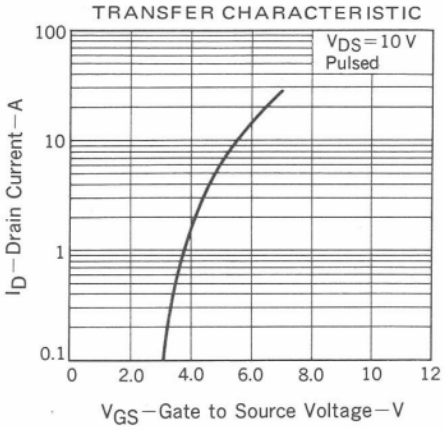
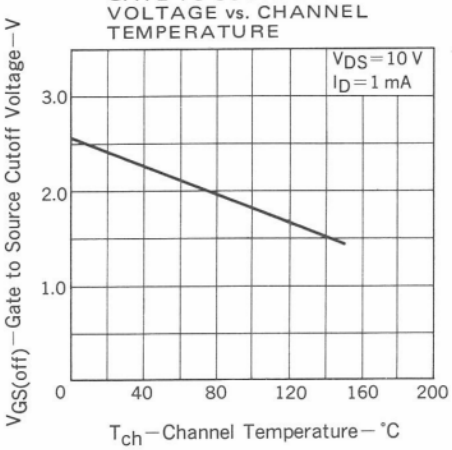
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



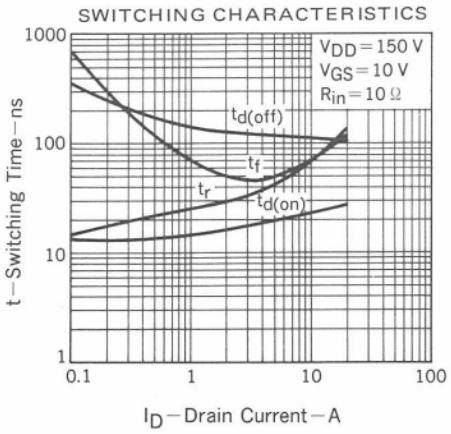
TRANSFER CHARACTERISTIC



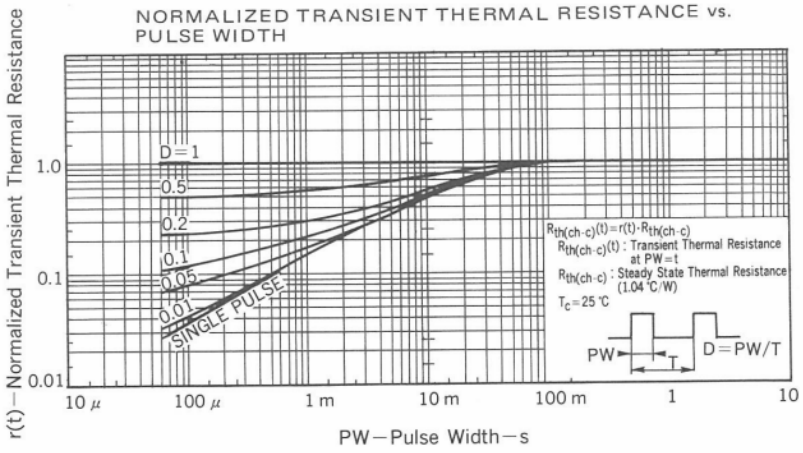
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



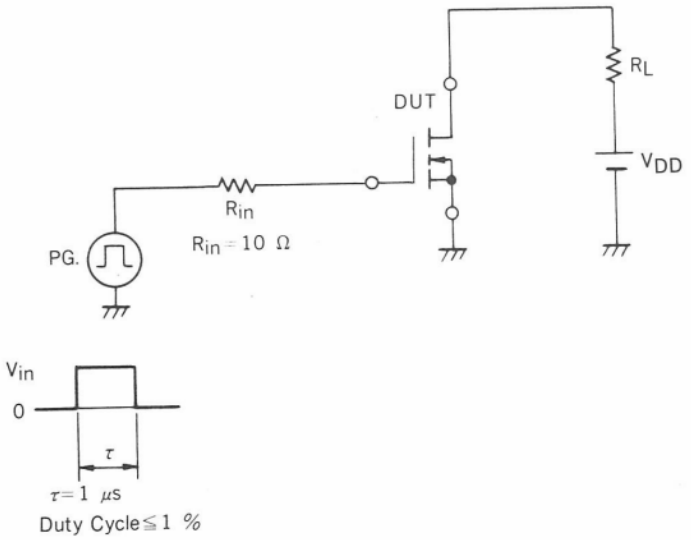
SWITCHING CHARACTERISTICS

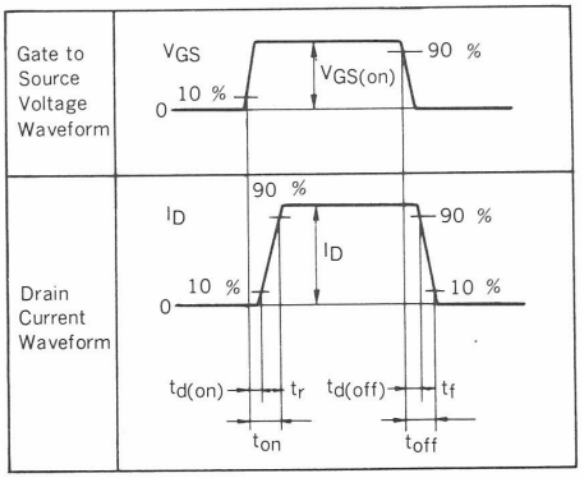


NORMALIZED TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



SWITCHING TIME TEST CIRCUIT





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Free Datasheet http://www.datasheet-pdf.com/